# BCM847BV; BCM847BS; BCM847DS

## **NPN/NPN** matched double transistors

Rev. 06 — 28 August 2009

**Product data sheet** 

## 1. Product profile

## 1.1 General description

NPN/NPN matched double transistors in small Surface-Mounted Device (SMD) plastic packages. The transistors are fully isolated internally.

Table 1. Product overview

Type number			PNP/PNP	Matched version of	
	NXP	JEITA	complement		
BCM847BV	SOT666	-	BCM857BV	BC847BV	
BCM847BS	SOT363	SC-88	BCM857BS	BC847BS	
BCM847DS	SOT457	SC-74	BCM857DS	-	

## 1.2 Features

- Current gain matching
- Base-emitter voltage matching
- Drop-in replacement for standard double transistors

## 1.3 Applications

- Current mirror
- Differential amplifier

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Per transistor								
$V_{CEO}$	collector-emitter voltage	open base	-	-	45	V		
I <sub>C</sub>	collector current		-	-	100	mA		
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V};$ $I_{C} = 2 \text{ mA}$	200	290	450			



Table 2. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
h <sub>FE1</sub> /h <sub>FE2</sub>	h <sub>FE</sub> matching	$V_{CE} = 5 \text{ V};$ $I_C = 2 \text{ mA}$	[1] 0.9	1	-	
$V_{BE1}-V_{BE2}$	V <sub>BE</sub> matching	$V_{CE} = 5 \text{ V};$ $I_{C} = 2 \text{ mA}$	[2] _	-	2	mV

<sup>[1]</sup> The smaller of the two values is taken as the numerator.

# 2. Pinning information

Table 3. **Pinning** 

14510 01	9			
Pin	Description	Simplified outline	Symbol	
1	emitter TR1		0 5 4	
2	base TR1	6   5   4	6 5 4	
3	collector TR2		TR2	
4	emitter TR2		(TR1)	
5	base TR2			
6	collector TR1	001aab555	1 2 3	
			sym020	

# 3. Ordering information

**Ordering information** Table 4.

Type number	Package	Package					
	Name	Description	Version				
BCM847BV	-	plastic surface-mounted package; 6 leads	SOT666				
BCM847BS	SC-88	plastic surface-mounted package; 6 leads	SOT363				
BCM847DS	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457				

# **Marking**

Table 5. **Marking codes** 

Type number	Marking code[1]
BCM847BV	3A
BCM847BS	M1*
BCM847DS	R6

<sup>[1] \* = -:</sup> made in Hong Kong

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<sup>[2]</sup> The smaller of the two values is subtracted from the larger value.

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

# 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{\text{CEO}}$	collector-emitter voltage	open base	-	45	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
Ic	collector current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT666		[1][2] -	200	mW
	SOT363		<u>[1]</u> _	200	mW
	SOT457		<u>[1]</u> _	250	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT666		[1][2]	300	mW
	SOT363		<u>[1]</u> _	300	mW
	SOT457		<u>[1]</u> _	380	mW
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

## 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Per transistor								
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air						
	SOT666		[1][2]	-	625	K/W		
	SOT363		[1] _	-	625	K/W		
	SOT457		[1] -	-	500	K/W		

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<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

 Table 7.
 Thermal characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Per device							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air					
	SOT666		[1][2]	-	416	K/W	
	SOT363		[1] _	-	416	K/W	
	SOT457		<u>[1]</u> _	-	328	K/W	

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

## 7. Characteristics

Table 8. Characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 30 \text{ V};$ $I_E = 0 \text{ A}$	-	-	15	nA
		$V_{CB} = 30 \text{ V};$ $I_{E} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V};$ $I_C = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V};$ $I_{C} = 10 \mu\text{A}$	-	250	-	
		$V_{CE} = 5 \text{ V};$ $I_{C} = 2 \text{ mA}$	200	290	450	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$	-	50	200	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$	-	200	400	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$	<u>[1]</u> -	760	-	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$	[1] -	910	-	mV
$V_{BE}$	base-emitter voltage	$V_{CE} = 5 \text{ V};$ $I_C = 2 \text{ mA}$	<sup>[2]</sup> 610	660	710	mV
		$V_{CE} = 5 \text{ V};$ $I_{C} = 10 \text{ mA}$	[2] _	-	770	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	1.5	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	11	-	pF

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<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

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Table 8. **Characteristics** ...continued T<sub>amb</sub> = 25 °C unless otherwise specified

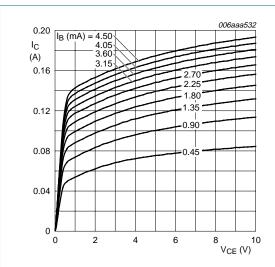
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V};$ $I_{C} = 10 \text{ mA};$ $f = 100 \text{ MHz}$	100	250	-	MHz
NF no	noise figure	$V_{CE} = 5 \text{ V};$ $I_{C} = 0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 10 \text{ Hz to}$ $15.7 \text{ kHz}$	-	2.8	-	dB
		$\begin{split} &V_{CE}=5 \text{ V;}\\ &I_{C}=0.2 \text{ mA;}\\ &R_{S}=2 \text{ k}\Omega;\\ &f=1 \text{ kHz;}\\ &B=200 \text{ Hz} \end{split}$	-	3.3	-	dB
Per device						
h <sub>FE1</sub> /h <sub>FE2</sub>	h <sub>FE</sub> matching	$V_{CE} = 5 V;$ $I_{C} = 2 \text{ mA}$	<u>[3]</u> 0.9	1	-	
$V_{BE1}-V_{BE2}$	V <sub>BE</sub> matching	$V_{CE} = 5 \text{ V};$ $I_{C} = 2 \text{ mA}$	[4] -	-	2	mV

<sup>[1]</sup>  $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.

<sup>[2]</sup>  $V_{BE}$  decreases by about 2 mV/K with increasing temperature.

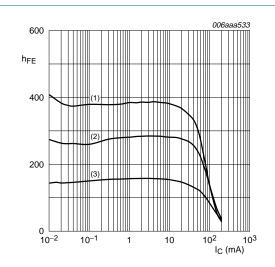
<sup>[3]</sup> The smaller of the two values is taken as the numerator.

<sup>[4]</sup> The smaller of the two values is subtracted from the larger value.



 $T_{amb} = 25 \, ^{\circ}C$ 

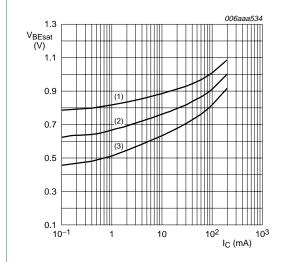
Fig 1. Collector current as a function of collector-emitter voltage; typical values



$$V_{CE} = 5 V$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

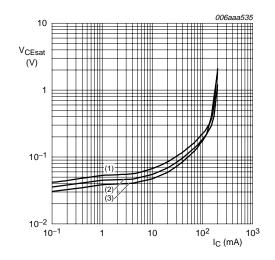
Fig 2. DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 3. Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

- (1) T<sub>amb</sub> = 100 °C
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 4. Collector-emitter saturation voltage as a function of collector current; typical values

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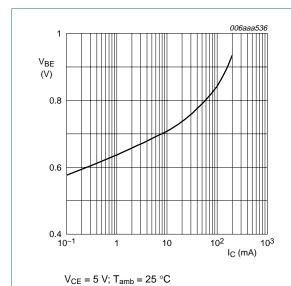
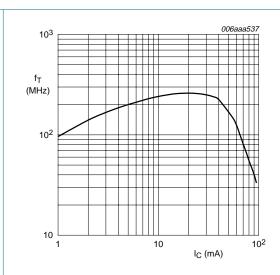


Fig 5. Base-emitter voltage as a function of collector current; typical values



 $V_{CE}$  = 5 V;  $T_{amb}$  = 25 °C Transition frequency as a function of collector

current; typical values

Fig 6.

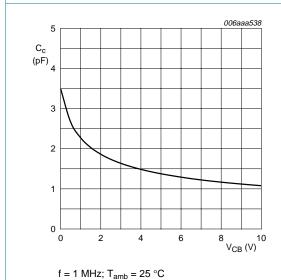
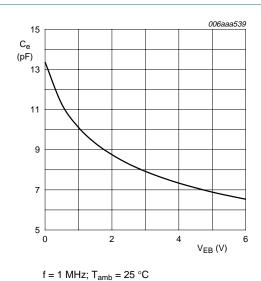


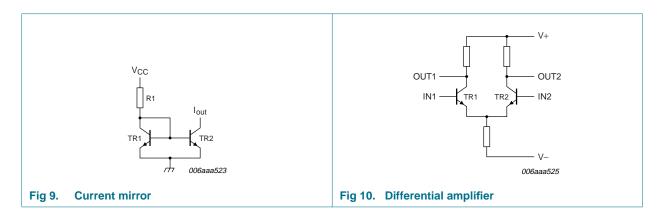
Fig 7. Collector capacitance as a function of collector-base voltage; typical values



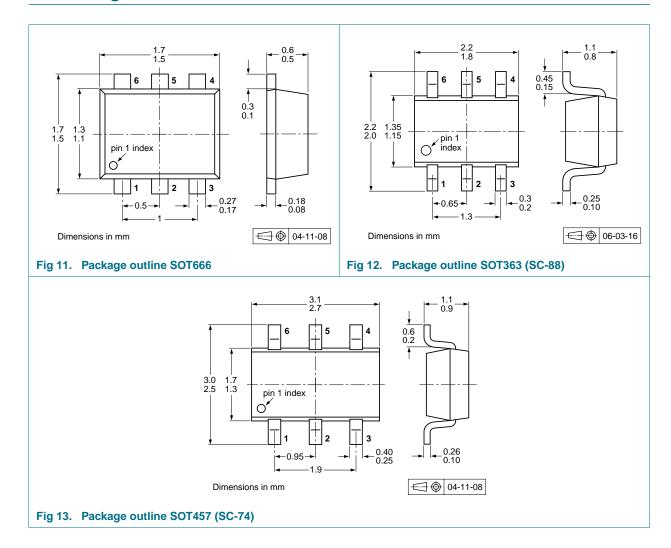
Emitter capacitance as a function of Fig 8. emitter-base voltage; typical values

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# 8. Application information



# 9. Package outline



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# 10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

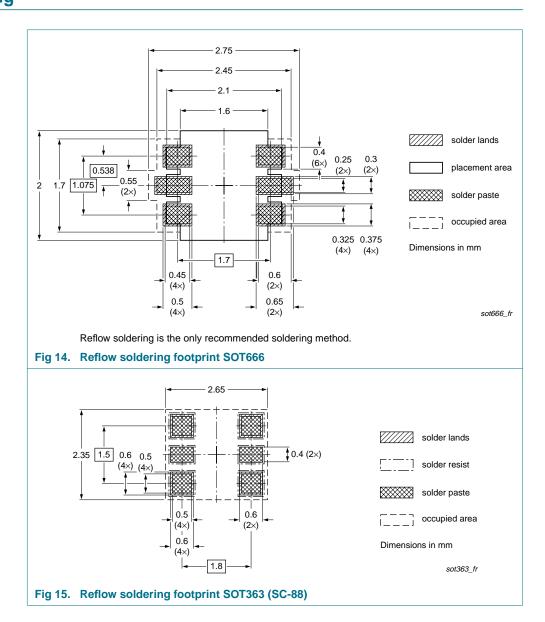
Type number	Package	Description		Packing quantity			
				3000	4000	8000	10000
BCM847BV	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
BCM847BS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165
BCM847DS	SOT457	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

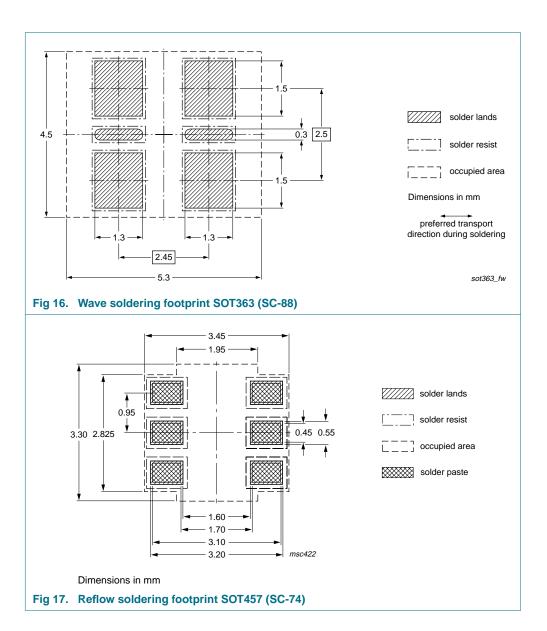
<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

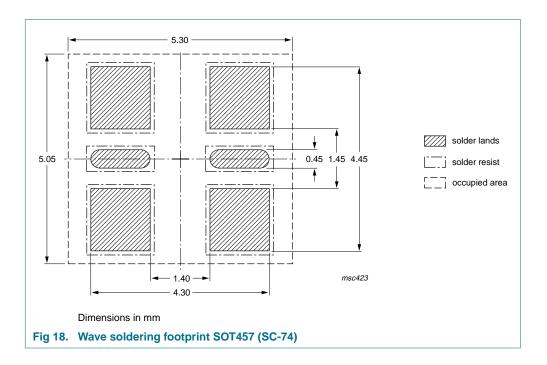
<sup>[2]</sup> T1: normal taping

<sup>[3]</sup> T2: reverse taping

## 11. Soldering







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# 12. Revision history

## Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BCM847BV_BS_DS_6	20090828	Product data sheet	-	BCM847BV_BS_DS_5			
Modifications:		eet was changed to reflec w legal definitions and disc					
	<ul><li>Figure 12 "P</li></ul>	ackage outline SOT363 (S	C-88)": updated				
	<ul><li>Figure 14 "R</li></ul>	deflow soldering footprint S	OT666": updated				
	<ul><li>Figure 15 "R</li></ul>	deflow soldering footprint S	SOT363 (SC-88)": update	ed			
	<ul><li>Figure 16 "V</li></ul>	Vave soldering footprint SC	OT363 (SC-88)": updated	I			
	<ul> <li>Figure 18 "Wave soldering footprint SOT457 (SC-74)": updated</li> </ul>						
BCM847BV_BS_DS_5	20060627	Product data sheet	-	BCM847BS_DS_4			
BCM847BS_DS_4	20060216	Product data sheet	-	BCM847BS_DS_3			
BCM847BS_DS_3	20060123	Product data sheet	-	BCM847BS_2			
BCM847BS_2	20050406	Product data sheet	-	BCM847BS_1			
BCM847BS_1	20040914	Product data sheet	-	-			

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## 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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# BCM847BV/BS/DS

## **NPN/NPN** matched double transistors

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